

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re PATENT Application of
 Akihiko ISHIBASHI et al
 Japanese Priority Application No. 11-299640
 Japanese Priority Date: October 21, 1999
 For: METHOD OF FABRICATING NITRIDE
 SEMICONDUCTOR DEVICE

)
) Art Unit Group: 2812
) Examiner: Savitri Mulpuri
)
) Date: July 10, 2002
)

H/Pre C
J. Steptae
7-16-02

RECEIVED
 JUL 11 2002
 1002800 MAIL ROOM

PRELIMINARY AMENDMENT

Commissioner for Patents
 Washington, D.C. 20231
 Sir:

Please preliminarily amend the subject application as follows:

IN THE CLAIM:

Please note that the amended claims are presented below in their amended form. It is further as an Attachment to the Amendment whereby the amendments to the specification is outlined using the conventional method of bracketing and underlining.

13. (AMENDED) A method of fabricating a nitride semiconductor device by a vapor deposition method comprising:

a step of growing , on a substrate, a first nitride semiconductor layer including magnesium under a first growth ambient pressure; and

a step of growing a second nitride semiconductor layer, which is adjacent to said first nitride semiconductor layer and does not include aluminum and magnesium, under a second growth ambient pressure,

wherein said first growth ambient pressure is lower than said second growth ambient pressure, and is lower than the atmospheric pressure
